

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

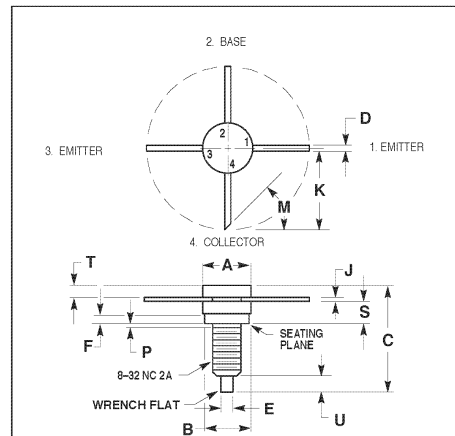
The **ASI MRF587** is Designed for High Linearity Power Amplifier Applications up to 500 MHz.

FEATURES:

- $P_e = 16$ dB Typical at 220 W/500 MHz
- Low Noise Figure
- Diffused Ballast Resistors
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CB0}	34 V
V_{CEO}	17 V
V_{EBO}	2.5 V
P_{DISS}	5.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C

PACKAGE STYLE .280 4NL STUD


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	7.06	7.26	0.278	0.286
B	6.20	6.50	0.244	0.256
C	15.24	16.51	0.600	0.650
D	0.66	0.86	0.026	0.034
E	1.40	1.65	0.055	0.065
F	1.52	—	0.060	—
J	0.10	0.15	0.004	0.006
K	11.17	—	0.440	—
M	45° NOM		45° NOM	
P	—	1.27	—	0.050
S	2.74	3.35	0.108	0.132
T	1.40	1.78	0.055	0.070
U	2.92	3.68	0.115	0.145

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	$I_C = 1.0$ mA	34			V
BV_{CEO}	$I_C = 5.0$ mA	17			V
BV_{EBO}	$I_E = 100$ μ A	2.5			V
I_{CB0}	$V_{CB} = 10$ V			50	μ A
h_{FE}	$V_{CE} = 5.0$ V $I_C = 50$ mA	50		200	---
C_{cb}	$V_{CB} = 10$ V $f = 1.0$ MHz		1.7	2.2	pF
G_P	$V_{CC} = 15$ V $I_C = 90$ mA $f = 0.3$ GHz	11	65		dB
η_C					

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